

**SCALABLE FLASH/NV STRUCTURES AND DEVICES  
WITH EXTENDED ENDURANCE**

**Abstract of the Disclosure**

5           Devices and methods are provided with respect to a gate stack for a  
nonvolatile structure. According to one aspect, a gate stack is provided. One  
embodiment of the gate stack includes a tunnel medium, a high K charge blocking  
and charge storing medium, and an injector medium. The high K charge blocking  
and charge storing medium is disposed on the tunnel medium. The injector medium  
10 is operably disposed with respect to the tunnel medium and the high K charge  
blocking and charge storing medium to provide charge transport by enhanced  
tunneling. According to one embodiment, the injector medium is disposed on the  
high K charge blocking and charge storing medium. According to one embodiment,  
the tunnel medium is disposed on the injector medium. Other aspects and  
15 embodiments are provided herein.

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